ON Semiconductor®

FDC642P

Single P-Channel 2.5V Specified PowerTrench® MOSFET

-20 V, -4.0 A, 65 mΩ

Features

- Max $r_{DS(on)}$ = 65 mΩ at V_{GS} = -4.5 V, I_D = -4.0 A
- Max $r_{DS(on)}$ = 100 mΩ at V_{GS} = -2.5 V, I_D = -3.2 A
- Fast switching speed
- Low gate charge (11nC typical)
- High performance trench technology for extremely low $r_{DS(on)}$
- SuperSOT™-6 package: small footprint (72% smaller than standard SO-8); low profile (1 mm thick)
- Termination is Lead-free and RoHS Compliant

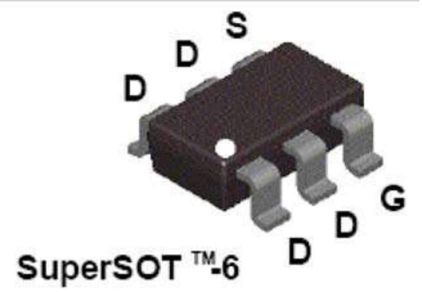
General Description

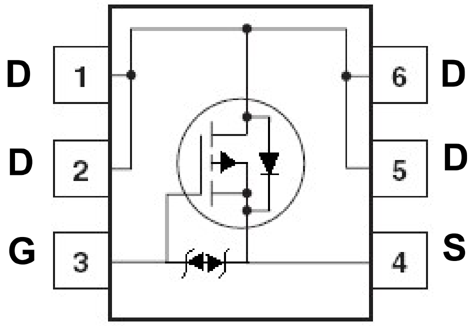
This P-Channel 2.5V specified MOSFET is produced using ON Semicondcutor's advanced PowerTrench® process that has been especially tailored to minimize on-state resistance and yet maintain low gate charge for superior switching performance.

These devices have been designed to offer exceptional power dissipation in a very small footprint for applications where the larger packages are impractical.

Applications

- Load switch
- Battery protection
- Power management





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter			Ratings	Units
V_{DS}	Drain to Source Voltage			-20	V
V_{GS}	Gate to Source Voltage			±8	V
I_D	-Continuous	T_A = 25°C	(Note 1a)	-4.0	A
	-Pulsed			-20	
P_D	Power Dissipation		(Note 1a)	1.6	W
	Power Dissipation		(Note 1b)	0.8	
T_J, T_{STG}	Operating and Storage Junction Temperature Range			-55 to + 150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	78	°C/W

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
.642	FDC642P	SSOT-6™	7 ”	8 mm	3000 units

October-2017, Rev. 3

Electrical Characteristics T_J = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units

Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	I_D = -250 µA, V_{GS} = 0 V	-20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = -250 µA, referenced to 25°C		-13		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = -16 V, V_{GS} = 0 V			-1	µA
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±8 V, V_{DS} = 0 V			±10	µA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = -250 µA	-0.4	-0.6	-1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = -250 µA, referenced to 25°C		2.5		mV/°C
$r_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = -4.5 V, I_D = -4.0 A		45	65	mΩ
		V_{GS} = -2.5 V, I_D = -3.2 A		55	100	
		V_{GS} = -4.5 V, I_D = -4.0 A, T_J = 125°C		62	90	
g_{FS}	Forward Transconductance	V_{DS} = -5 V, I_D = -4.0 A		15		S

Dynamic Characteristics

C_{iss}	Input Capacitance	V_{DS} = -10 V, V_{GS} = 0 V, f = 1 MHz		700	925	pF
C_{oss}	Output Capacitance			110	150	pF
C_{rss}	Reverse Transfer Capacitance			95	145	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	V_{DD} = -10 V, I_D = -1 A, V_{GS} = -4.5 V, R_{GEN} = 6 Ω		6	12	ns
t_r	Rise Time			7	14	ns
$t_{d(off)}$	Turn-Off Delay Time			120	190	ns
t_f	Fall Time			52	83	ns
Q_g	Total Gate Charge	V_{DD} = -10 V, I_D = -4 A V_{GS} = --4.5 V		11	16	nC
Q_{gs}	Gate to Source Charge			1.1		nC
Q_{gd}	Gate to Drain “Miller” Charge			3.0		nC

Drain-Source Diode Characteristics

I_S	Maximum Continuous Drain-Source Diode Forward Current				-1.3	A
V_{SD}	Source-Drain Diode Forward Voltage	V_{GS} = 0 V, I_S = -1.3 A (Note 2)		-0.7	-1.2	V

Notes:

1: $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.

a. 78 °C/W when mounted on a 1 in^2 pad of 2 oz copper.
b. 156°C/W when mounted on a minimum pad of 2 oz copper.

2: Pulse Test: Pulse Width<300 us, Duty Cycle<2.0%.

Typical Characteristics T_J = 25°C unless otherwise noted

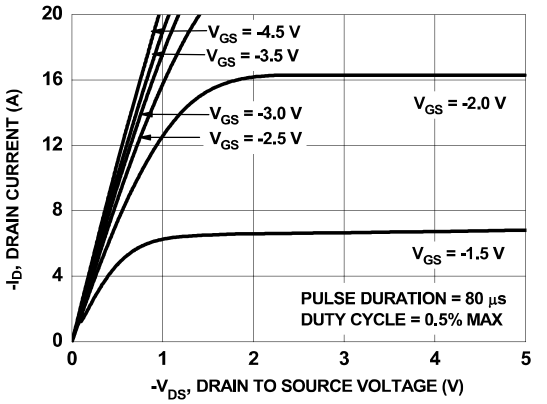


Figure 1. On Region Characteristics

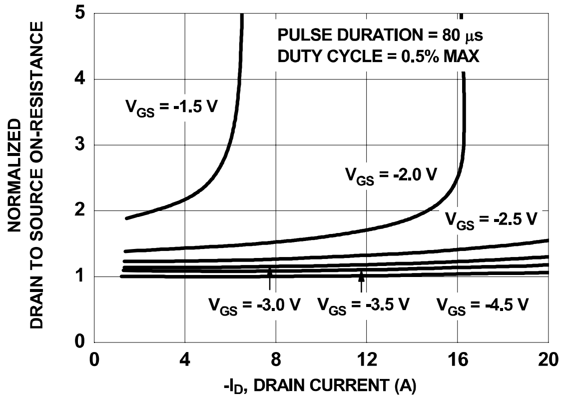


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

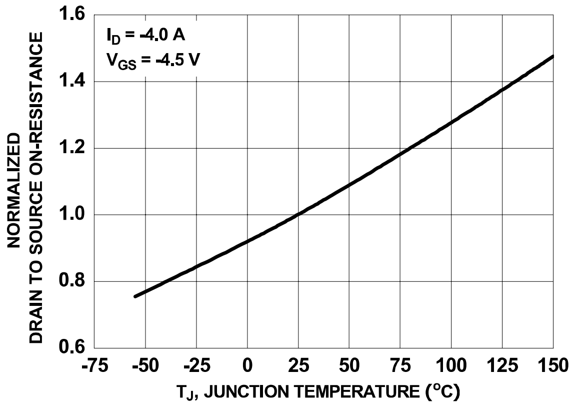


Figure 3. Normalized On Resistance vs Junction Temperature

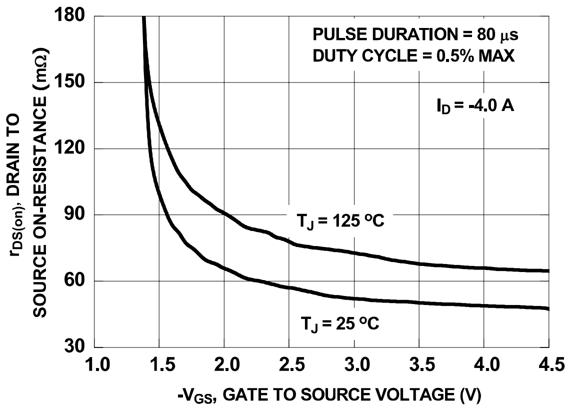


Figure 4. On-Resistance vs Gate to Source Voltage

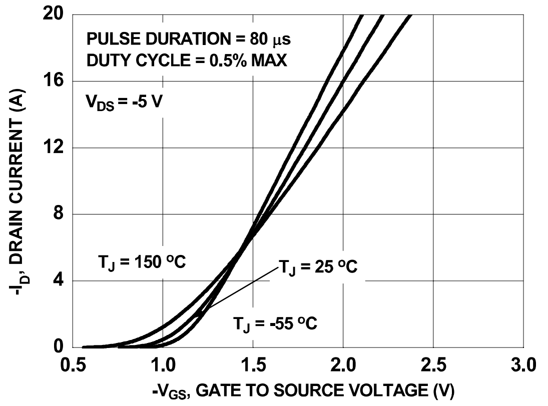


Figure 5. Transfer Characteristics

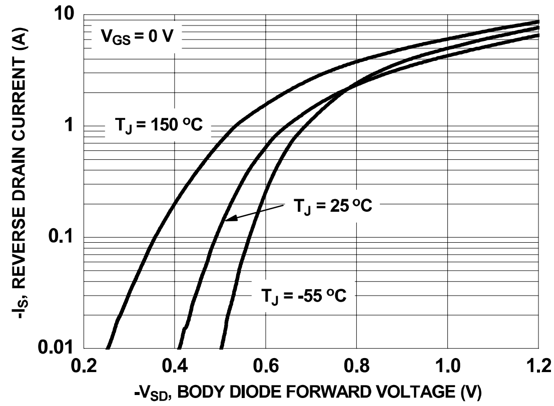


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics T_J = 25°C unless otherwise noted

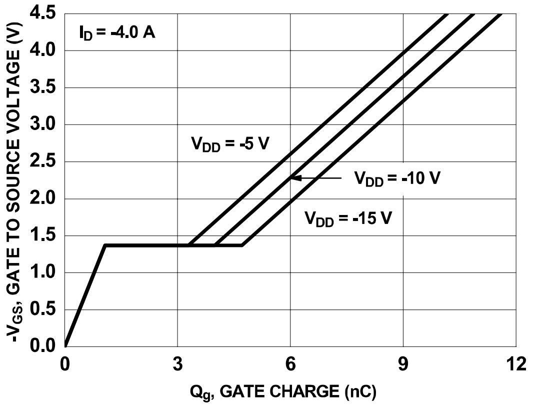


Figure 7. Gate Charge Characteristics

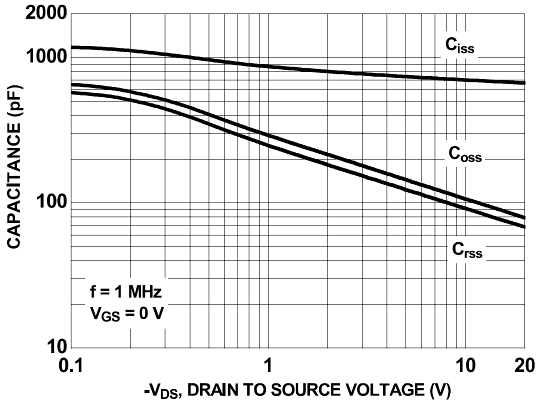


Figure 8. Capacitance vs Drain to Source Voltage

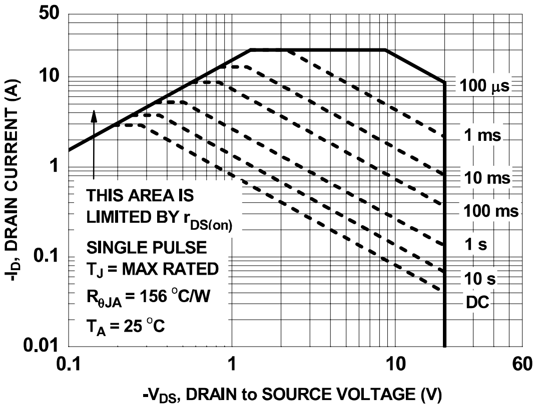


Figure 9. Forward Bias Safe Operating Area

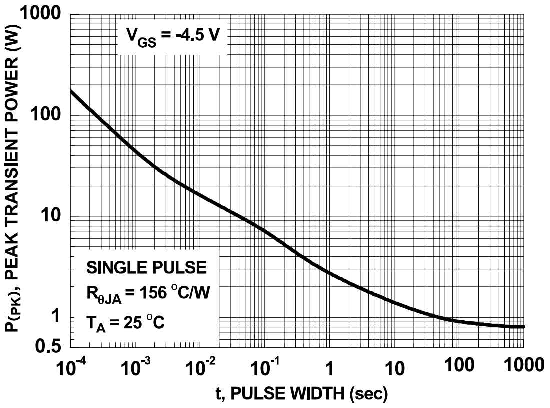


Figure 10. Single Pulse Maximum Power Dissipation

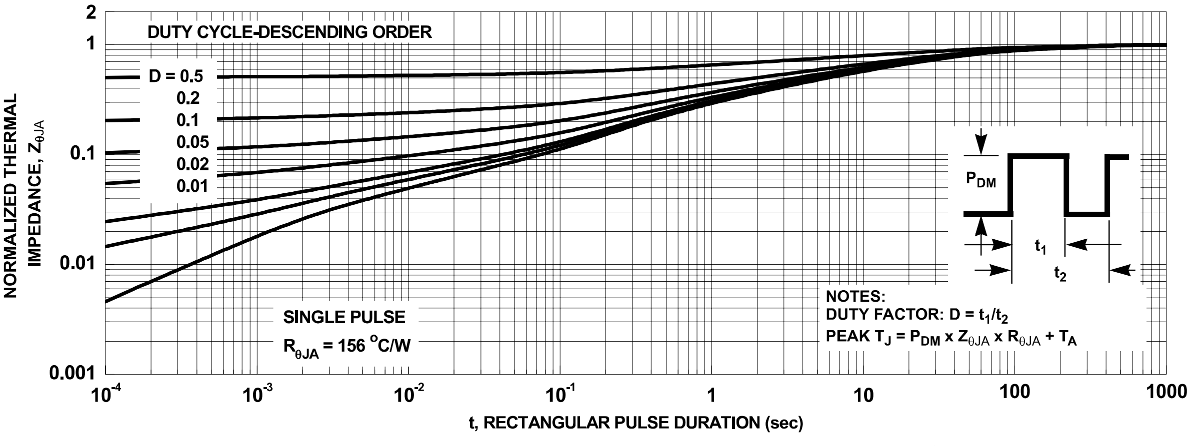


Figure 11. Junction-to-Ambient Transient Thermal Response Curve

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